# MGFC44V5964

# 5.9~6.4GHz BAND 24W INTERNALLY MATCHED GaAs FET

### **DESCRIPTION**

The MGFC44V5964 is an internally impedance-matched GaAs power FET especially designed for use in  $5.9 \sim 6.4$  GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

- Class A operation
- Internally matched to  $50\Omega$  system
- High output power

 $P_{1dB} = 24W (TYP) @ 5.9 \sim 6.4 GHz$ 

High power gain

 $G_{LP} = 9 \text{ dB (TYP)} @ 5.9 \sim 6.4 \text{ GHz}$ 

High power added efficiency

 $\eta_{\rm add} = 33\% \, ({\rm TYP}) \, @ \, 5.9 \sim 6.4 \, {\rm GHz}$ 

· Hermetically sealed metal-ceramic package

• Low distortion [Item: -51]

 $IM_3 = -42dBc(MIN)@Po=33.5(dBm) S.C.L.$ 

#### **APPLICATION**

Item -01: 5.9  $\sim$  6.4 GHz band power amplifier

Item -51: Digital radio communication

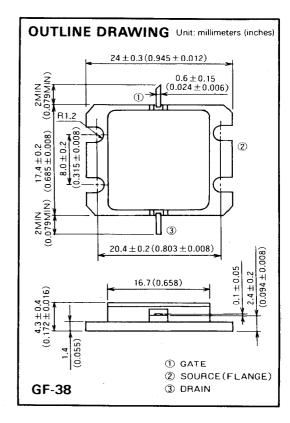
### **QUALITY GRADE**

• IG

### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter Ratings		Unit
V <sub>GDO</sub>	Gate to drain voltage	-15	٧
V <sub>GSO</sub>	Gate to source voltage	-15	٧
I <sub>D</sub>	Drain current	20	Α
I <sub>GR</sub>	Reverse gate current	-60	mA
I <sub>GF</sub>	Forward gate current	126	mA
PT	Total power dissipation +1	93	w
Tch	Channel temperature	175	°C
Tstg	Storage temperature	<b>−65~+175</b>	°C

<sup>\*1:</sup> T<sub>c</sub> = 25°C



### **RECOMMENDED BIAS CONDITIONS**

- V<sub>DS</sub>=10V
- I<sub>D</sub>= 6.4A
- Rg=25 Q
- Refer to Bias Procedure

### ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			1,
	raiametei	rest conditions	Min	Тур	Max	Unit
IDSS	Saturated drain current	V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	_	18	_	А
9m	Transconductance	V <sub>DS</sub> =3V, I <sub>D</sub> =6.4A	_	6.5	_	S
VGS(off)	Gate to source cut-off voltage	V <sub>DS</sub> =3V, I <sub>D</sub> = 120mA	-2	_	-5	V
P <sub>1dB</sub>	Output power at 1dB gain compression		43	44	_	dBm
GLP	Linear power gain	V <sub>DS</sub> = 10V, I <sub>D</sub> =6.4A, f=5.9~6.4GHz	8	9	_	dB
7add	Power added efficiency			33	_	%
IM <sub>3</sub>	3rd order IM distortion #1		-42		_	dBc
Rth (ch-c)	Thermal resistance #2	$\Delta V_{f}$ method	_	_	1.6	°C/W

<sup>\*1:</sup> Item-51, 2-tone test  $P_0 = 33.5 \text{ dBm}$  Single Carrier Level f = 6.4 GHz  $\Delta f = 10 \text{ MHz}$ , \*2: Channel to case



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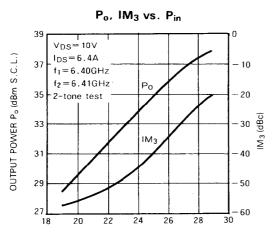
## TYPICAL CHARACTERISTICS (Ta=25℃)

P<sub>1dB</sub>, G<sub>LP</sub> vs. f  $V_{DS} = 10V$ P<sub>1dB</sub> IDS=6.4 A 12 44 OUTPUT POWER P<sub>1dB</sub> (dBm) LINEAR POWER GAIN GLP (dB) 43  $G_{\mathsf{LP}}$ 42 41 40 6.1 6.2 6.3

 $V_{DS} = 10V$ IDS=6.4A POWER ADDED EFFICIENCY  $\eta_{\rm add}$  (%) Рο f = 6,15GHz 40 40 OUTPUT POWER Po (dBm) 35 30  $\eta_{add}$ 30 20 25 20 35 15 20 • 25 40 INPUT POWER Pin (dBm)

 $P_o,\;\eta_{add}\;vs.\;P_{in}$ 

FREQUENCY f (GHz)



INPUT POWER Pin (dBm S.C.L.)

### **S PARAMETERS** (Ta = 25°C, $V_{DS} = 10$ V, $I_{DS} = 6.4$ A)

f (GHz)	S Parameter (TYP.)							
	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)	Magn.	Angle (deg.)
5.9	0.48	117	2.79	- 61	0.033	- 114	0.32	164
6.0	0.43	98	2.81	- 79	0.046	- 141	0.35	145
6.1	0.36	78	2.84	97	0.052	- 152	0.37	127
6.2	0.28	54	2.81	- 115	0.062	- 174	0.38	108
6.3	0.21	27	, 2.79	- 132	0.070	167	0.39	96
6.4	0.13	- 9	2.77	<b>– 150</b>	0.078	149	0.40	80

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